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Negative Voltage SPDT Switch

The NLHV4157N is an advanced CMOS analog switch fabricated with silicon gate CMOS technology. The device passes analog and digital negative voltages that may vary across the full power–supply range (from V_{EE} to GND).

Features

- Operating Voltage Range: $V_{EE} = -12 \text{ V}$ to -4 V
- Switch Signal Voltage Range: $V_{IS} = V_{EE}$ to GND
- Positive Control Signal Voltage: $V_{IN} = 0$ to 3.3 V
- Low ON Resistance: $R_{ON} \le 5 \Omega$ @ $V_{EE} = -10 \text{ V}$
- Latch-up Performance Exceeds 200 mA
- Available in: SC-88 6-Pin Package
- These Devices are Pb–Free, Halogen–Free/BFR-Free and are RoHS–Compliant

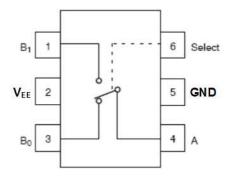


Figure 1. Pin Assignment and logic Diagram



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MARKING DIAGRAM



SC-88 DF SUFFIX CASE 419B



HW = Device Code M = Date Code* ■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

FUNCTION TABLE

| Select Input | Function |
|--------------|-------------------|
| L | B0 Connected to A |
| Н | B1 Connected to A |

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|----------------|--------------------|-----------------------|
| NLHV4157NDFT2G | SC-88 (Pb-Free) | 3000 / Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

MAXIMUM RATINGS

| Symbol | Ra | ting | Value | Unit |
|-------------------|---|--|------------------------------|------|
| V _{EE} | DC Supply Voltage | | -13 to +0.5 | V |
| V _{IS} | Analog Input Voltage (Note 1) | | V _{EE} -0.5 to +0.5 | V |
| V _{IN} | N Digital Select Input Voltage (Note 1) | | -0.5 to +3.6 | V |
| I _{IOK} | Switch Input/Output diode current | ±50 | mA | |
| I _{IK} | Select input diode current | – 50 | mA | |
| P_{D} | Power Dissipation in Still Air | | 60 | mW |
| TL | Lead Temperature, 1 mm from Case for | or 10 seconds | 260 | °C |
| TJ | Junction Bias Under Bias | | 150 | °C |
| MSL | Moisture Sensitivity | | Level 1 | |
| F _R | Flammability Rating | Oxygen Index: 30% – 35% | UL94-V0 (0.125 in) | °C |
| ΙL | Latch-up Current (Note1) | Below GND and above V _{EE} at 125°C | ±200 | mA |
| | | Below GND and above V _{EE} at 25°C | ±300 | |
| T _s | Storage Temperature | | -65 to +150 | °C |
| $\theta_{\sf JA}$ | Thermal Resistance | 400 | °C/W | |
| ESD | ESD Protection | Human Body Model | 3000 | V |
| | | Machine Model | 150 | 1 |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The input and output voltage ratings may be exceeded if the input and output diode current ratings are observed.

RECOMMENDED OPERATING CONDITIONS (Note 2)

| Symbol | Parameter | Min | Max | Unit |
|---------------------------------|---|----------|------|------|
| V_{EE} | DC Supply Voltage | -12 | -4 | V |
| V _S | Switch Input / Output Voltage (B0, B1, A) | V_{EE} | GND | V |
| V _{IN} | Digital Select Input Voltage | GND | 3.3 | V |
| T_A | Operating Temperature Range | -55 | +125 | °C |
| t _r , t _f | Input Transition Rise or Fall Time (Select Input) | 0 | 100 | ns/V |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

2. Select input must be held HIGH or LOW, it must not float.

DC ELECTRICAL CHARACTERISTICS (Voltages referenced to GND: Typical characteristics are T_A at 25°C.)

| | | | | : | –55° to 125° | | _ |
|--|--|--|---------------------|-----|--|------|-----|
| Symbol | Parameter | Condition | V _{EE} , V | Min | Тур | Max | Uni |
| SELECT IN | PUT | | | | | | |
| V _{IH} | Minimum High-Level | | -12 | 1.8 | 3.3 3.3 3.3 3.3 3.3 3.3 3.3 3.3 3.3 3.3 | V | |
| | Input Voltage | | -10 | 1.6 | | 3.3 | |
| | | | -8 | 1.4 | | 3.3 | |
| | | | -6 | 1.2 | | 3.3 | |
| | | | -4 | 1.0 | | 3.3 | |
| V _{IL} | Maximum Low-Level | | -12 | 0 | | 0.8 | ٧ |
| | Input Voltage | | -10 | 0 | | 0.7 | |
| | | | -8 | 0 | | 0.6 | |
| | | | -6 | 0 | | 0.5 | 1 |
| | | | -4 | 0 | | 0.4 | |
| I _{IN} | Maximum Input Leakage | V _{IN} = 3.3 V or GND | -10 | | ±0.2 | ±50 | μ |
| | Current | V _{IN} = 3.3 V or GND, test at 25°C only | -10 | | | ±0.5 | 1 |
| POWER SU | JPPLY | | | | | | |
| I _{CC} | Maximum Quiescent Supply Current | Select = 3.3 V or GND, V _{IS} = V _{EE} or GND | -10 to -4 | | 25 | 80 | μ |
| ANALOG S | WITCH | | • | | • | • | |
| R _{ON} | Maximum ON Resistance (Note 3) | $V_{IN} = V_{IL} \text{ or } V_{IH}$ $V_{IS} = V_{EE} \text{ to GND}$ $I_O \le 10 \text{ mA}$ | -12 | | 2.6 | 4.5 | 9 |
| | | | -10 | | 3.0 | 5 | 1 |
| | | | -8 | | 3.5 | 5.8 | 1 |
| | | | -6 | | 4.5 | 7.5 | |
| | | $V_{IN} = V_{IL}$ or V_{IH} $V_{IS} = V_{EE}$ to GND $I_{O} \le 5$ mA | -4 | | 9 | 15 | |
| R _{FLAT} | ON Resistance | $V_{IN} = V_{IL}$ or V_{IH} | -12 | | 0.4 | | Ω |
| | Flatness (Notes 3, 4, 6) | $V_{IS}^{IN} = V_{EE}^{IE}$ to GND $I_{O} \le 10$ mA | -10 | | 1.2 | | |
| | | .0 = .0 | -8 | | 1.7 | | |
| | | | -6 | | 2.5 | | |
| | | $V_{IN} = V_{IL} \text{ or } V_{IH}$ $V_{IS} = V_{EE} \text{ to GND}$ $I_O \le 5 \text{ mA}$ | -4 | | 6 | | |
| ΔR_{ON} | R _{ON} Mismatch | $I_A = -10 \text{ mA}, V_{Bn} = -8.4 \text{ V}$ | -12 | | Typ Max 3.3 3.3 3.3 3.3 3.3 3.3 3.3 3.3 3.3 3 | Ω | |
| | Between (Notes 3, 4, 5) | $I_A = -10 \text{ mA}, V_{Bn} = -7 \text{ V}$ | -10 | | | | |
| | | I _A = -10 mA, V _{Bn} = -5.6 V | -8 | | 0.25 | | |
| | | $I_A = -10 \text{ mA}, V_{Bn} = -4.2 \text{ V}$ | -6 | | 0.25 | | |
| | | $I_A = -5 \text{ mA}, V_{Bn} = -2.8 \text{ V}$ | -4 | | 0.3 | | 1 |
| I _{NC(OFF)} , I _{NO(OFF)} | NC or NO OFF Leakage Current (Figure 9) | $V_{IN} = V_{IL}$ or V_{IH} , $V_{Bn} = GND$, $V_A = V_{EE}$ to GND | -10 | | ±1.0 | ±20 | μ |
| I _{COM(ON)} | COM ON Leakage Current (Figure 9) | $\begin{aligned} &V_{IN} = V_{IL} \text{ or } V_{IH}; \\ &V_A = \text{GND V or } V_{EE}; \\ &V_{B1} = \text{GND or } V_{EE} \text{ with } V_{B0} \text{ floating, or } \\ &V_{B0} = \text{GND or } V_{EE} \text{ with } V_{B1} \text{ floating} \end{aligned}$ | -10 | | ±2.0 | ±20 | μ |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Measured by the voltage drop between A and B pins at the indicated current through the switch. On Resistance is determined by the lower

of the voltages on the two (A or B Ports).

4. Parameter is characterized but not tested in production.

ΔR_{ON} = R_{ON}min measured at identical V_{EE}, temperature and voltage levels.
 Flatness is defined as the difference between the maximum and minimum value of ON Resistance over the specified range of conditions.

$\textbf{AC ELECTRICAL CHARACTERISTICS} \ (Voltages \ referenced \ to \ GND; \ Typical \ characteristics \ are \ T_A \ at \ 25^{\circ}C.)$

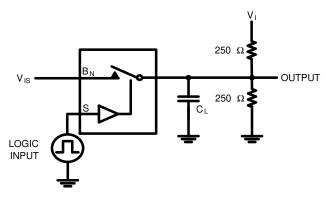
| | | | | -55° to 125°C | | С | |
|-------------------------------------|---|---|---------------------|---------------|-----|-----|------|
| Symbol | Parameter | Condition | V _{EE} , V | Min | Тур | Max | Unit |
| t _{PHL} , t _{PLH} | Propagation Delay, Bus to Bus (Note 8) (A to B _n) | C _L = 100 pF (Figures 2, 3) | −12 to −4 | | | 2 | ns |
| t_{PZL},t_{PZH} | Switch Enable Time | C _L = 100 pF (Figures 2, 3) | -12 | | | 220 | ns |
| | Turn-On Time (A to B _n) | | -10 | | | 175 | |
| | (* 1.10 = 1)) | | -8 | | | 165 | |
| | | | -6 | | | 165 | |
| | | | -4 | | | 200 | |
| t_{PLZ},t_{PHZ} | Switch Disable Time | C _L = 100 pF (Figures 2, 3) | -12 | | | 225 | ns |
| | Turn-Off Time (A to B _n) | | -10 | | | 155 | |
| | (A to B _n) | | -8 | | | 150 | |
| | | | -6 | | | 120 | |
| | | | -4 | | | 145 | |
| t _B | Switch Break Time | $R_L = 50 \Omega, C_L = 100 pF,$ | -12 | 5 | 60 | 60 | ns |
| | | $V_{IS} = -2.5 \text{ V (Figure 4)}$ | -10 | 5 | | 60 | |
| | | | -8 | 10 | | 75 | |
| | | | -6 | 10 | | 90 | |
| | | | -4 | 40 | | 135 | |
| t _{POR} | Power ON Reset Time | Measured from V _{EE} = -4 V | −12 to −4 | | | 20 | μS |
| Q | Charge Injection | $C_L = 1 \text{ nF, } V_{GEN} = 0 \text{ V,}$ | -12 | | 170 | | pC |
| | (Note 7) | $R_{GEN} = 0 \Omega $ (Figure 5) | -10 | | 120 | | |
| | | | -8 | | 95 | | |
| | | -6 | | 55 | | | |
| | | | -4 | | 40 | | |
| OIRR | Off-Isolation (Note 9) | $R_L = 50 \Omega$, $f = 10 MHz$ (Figure 6) | −12 to −4 | | -33 | | dB |
| Xtalk | Crosstalk | $R_L = 50 \Omega$, f = 10 MHz (Figure 7) | −12 to −4 | | -42 | | dB |
| BW | –3 dB Bandwidth | $R_L = 50 \Omega$ (Figure 10) | −12 to −4 | | 200 | | MHz |

CAPACITANCES (Note 10)

| Symbol | Parameter | Test Conditions | Typical @ 25°C | Unit |
|---------------------|---|--------------------------|----------------|------|
| C _{IN} | Input Capacitance, Select Inputs | V _{EE} = -12 V | 6 | pF |
| C _{IOB} | B-Port OFF Capacitance | $V_{EE} = -10 \text{ V}$ | 45 | pF |
| C _{IOA_ON} | A Port Capacitance when Switch is Enabled | $V_{EE} = -10 \text{ V}$ | 100 | pF |

 $^{10.}T_A = +25$ °C, f = 1 MHz, Capacitance is characterized but not tested in production.

Guaranteed by Design.
 This parameter is guaranteed by design but not tested. The bus switch contributes no propagation delay other than the RC delay of the ON Resistance of the switch and the 50 pF load capacitance, when driven by an ideal voltage source (zero output impedance).
 Off Isolation = 20 log10 [VA/VBn].



Note: Input V_{IS} driven by 50 Ω source terminated by 50 Ω . Note: C_L includes load and stray capacitance. Input PRR = 100 kHz, t_W = 5 μ s.

| Parameter | VI | V _{IS} |
|-------------------------------------|---------------------|-----------------|
| t _{PLH} / t _{PHL} | Open | Source |
| t _{PZL} / t _{PLZ} | GND | V _{EE} |
| t _{PZH} / t _{PHZ} | 2 x V _{EE} | GND |

Figure 2. AC Test Circuit

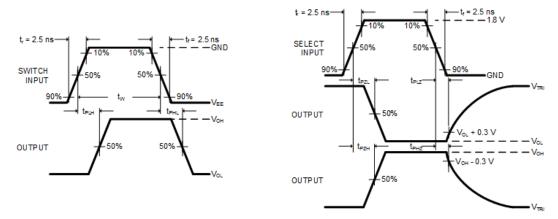


Figure 3. AC Test Waveforms

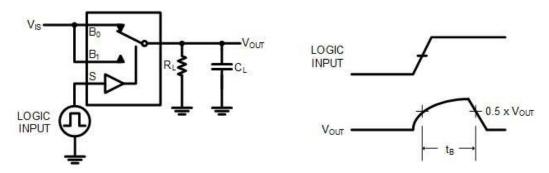
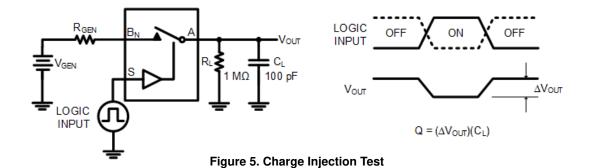


Figure 4. Switch Break Interval Timing



Analyzer

B₀ or B₁

B₁ or B₀

Signal Generator odem

LOGIC INPUT
0 V or V_{IH}

Figure 6. Off Isolation

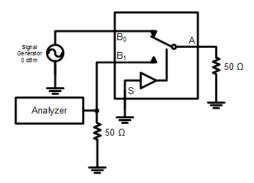


Figure 7. Crosstalk

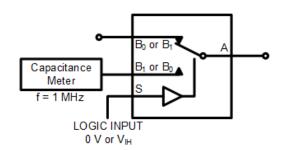


Figure 8. Channel Off Capacitance

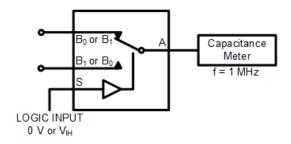


Figure 9. Channel On Capacitance

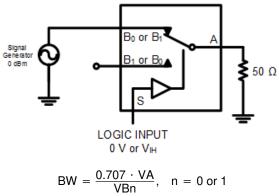


Figure 10. Bandwidth

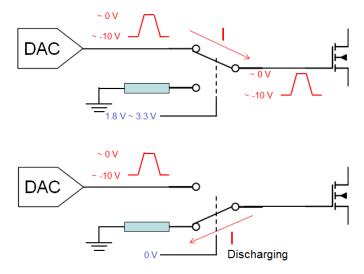
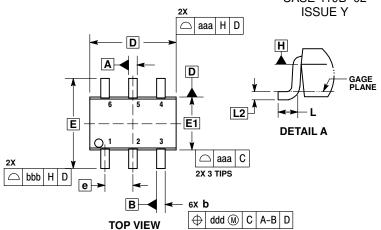
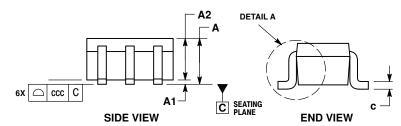


Figure 11. Typical Application

PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363 CASE 419B-02





- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.
 DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.

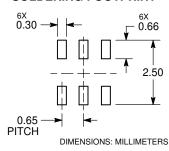
 DATUMS A AND B ARE DETERMINED AT DATUM H.

 DIMENSIONS A AND BARD ADDIT OF THE LAT SECTION OF THE

- DIMENSIONS 6 AND 6 APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
- DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION.
 ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION DAT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

| | MILLIMETERS | | | | INCHES | 3 |
|-----|-------------|---------|-------|-----------|--------|-------|
| DIM | MIN | NOM | MAX | MIN | NOM | MAX |
| Α | | | 1.10 | | | 0.043 |
| A1 | 0.00 | | 0.10 | 0.000 | | 0.004 |
| A2 | 0.70 | 0.90 | 1.00 | 0.027 | 0.035 | 0.039 |
| b | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 |
| С | 0.08 | 0.15 | 0.22 | 0.003 | 0.006 | 0.009 |
| D | 1.80 | 2.00 | 2.20 | 0.070 | 0.078 | 0.086 |
| E | 2.00 | 2.10 | 2.20 | 0.078 | 0.082 | 0.086 |
| E1 | 1.15 | 1.25 | 1.35 | 0.045 | 0.049 | 0.053 |
| е | | 0.65 BS | С | 0.026 BSC | | |
| L | 0.26 | 0.36 | 0.46 | 0.010 | 0.014 | 0.018 |
| L2 | | 0.15 BS | C | 0.006 BSC | | |
| aaa | 0.15 | | | 0.006 | | |
| bbb | 0.30 | | 0.012 | | | |
| ccc | 0.10 | | | 0.004 | | |
| ddd | | | | | | |

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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